

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

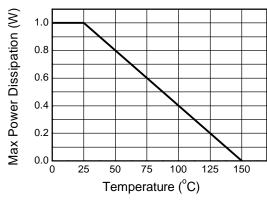
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	3	Α
Peak Pulse Collector Current	I _{CM}	6	Α
Peak Base Current	I _B	500	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	D-	1	W	
Fower Dissipation	(Note 7)	P _D	2	VV	
Thermal Resistance, Junction to Ambient Air	(Note 6)	0	125	°C/W	
	(Note 7)	R _{0JA}	62.5		
Thermal Resistance, Junction to Leads	(Note 8)	$R_{ heta JL}$	6.0	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

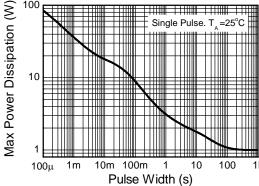
- 6. For a device surface mounted on 15mm x 15mm x 0.6mm FR-4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in steady state condition.
- 7. Same as note 6, except the device is mounted on 40mm x 40mm x 1.6mm FR-4 PCB.
- 8. Thermal resistance from junction to solder-point (on the exposed collector pad).

Thermal Characteristics and Derating Information



Thermal Resistance (°C/W) 120 80 20 10 Pulse Width (s)

Transient Thermal Impedance Derating Curve



Pulse Power Dissipation



Electrical Characteristics (@T_A = ±25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	80			V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	60	_	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	5			V	$I_E = 100 \mu A$
Collector-Base Cutoff Current	I _{CBO}	_		0.1 10	μΑ	$V_{CB} = 60V$ $V_{CB} = 60V$, $T_{A} = +100$ °C
Emitter-Base Cutoff Current	I _{EBO}	_	_	0.1	μΑ	$V_{EB} = 4V$
ON CHARACTERISTICS (Note 9)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.08 0.23	0.3 0.6	V	$I_C = 1A$, $I_B = 100mA$ $I_C = 3A$, $I_B = 300mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	0.85	1.25	V	$I_C = 1A$, $I_B = 100mA$
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	0.8	1	V	$V_{CE} = 2V$, $I_C = 1A$
DC Current Gain	h _{FE}	70 100 80 40	200 200 185 120	 300 	l	$V_{CE} = 2V, I_{C} = 50mA$ $V_{CE} = 2V, I_{C} = 500mA$ $V_{CE} = 2V, I_{C} = 1A$ $V_{CE} = 2V, I_{C} = 2A$
SMALL-SIGNAL CHARACTERISTICS						
Transition Frequency	f⊤	140	200		MHz	$V_{CE} = 5V$, $I_{C} = 100mA$, $f = 100MHz$
Output Capacitance	C _{obo}		_	30	pF	$V_{CB} = 10V$, $f = 1MHz$
Switching Times	t _{ON} t _{OFF}	_	35 230	_	ns ns	$V_{CC} = 10V$. $I_C = 500mA$, $I_{B1} = -I_{B2} = 50mA$

Note:

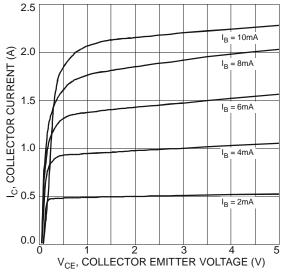


Figure 1 Typical Collector Current vs. Collector-Emitter Voltage

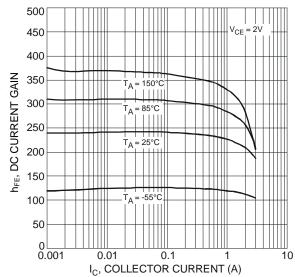


Figure 2 Typical DC Current Gain vs. Collector Current

^{9.} Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



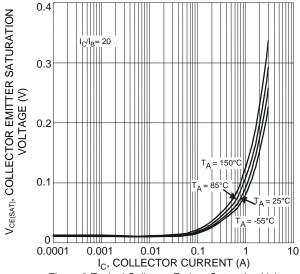


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

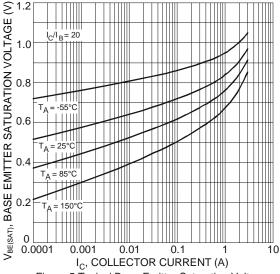


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

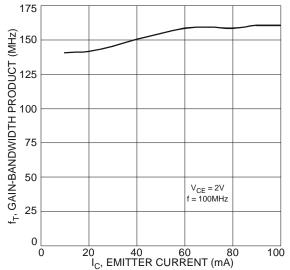


Figure 7 Typical Gain-Bandwidth Product vs. Emitter Current

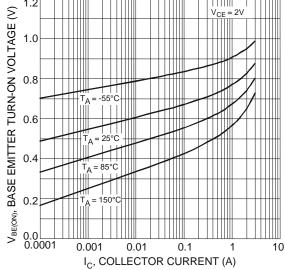


Figure 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

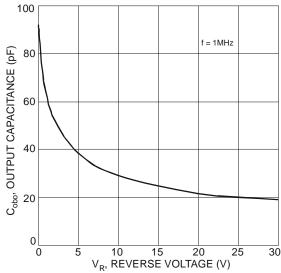
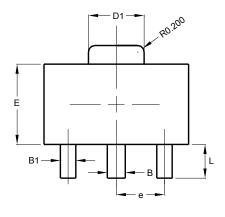


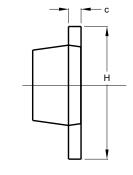
Figure 6 Typical Output Capacitance Characteristics

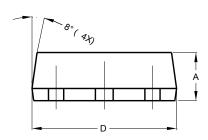


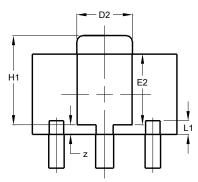
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.





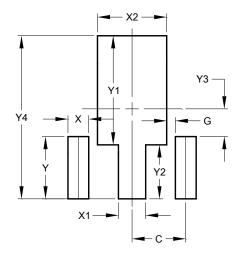




SOT89				
Dim	Min	Max	Тур	
Α	1.40	1.60	1.50	
В	0.50	0.62	0.56	
B1	0.42	0.54	0.48	
С	0.35	0.43	0.38	
D	4.40	4.60	4.50	
D1	1.62	1.83	1.733	
D2	1.61	1.81	1.71	
Е	2.40	2.60	2.50	
E2	2.05	2.35	2.20	
е	1	-	1.50	
Н	3.95	4.25	4.10	
H1	2.63	2.93	2.78	
L	0.90	1.20	1.05	
L1	0.327	0.527	0.427	
Z	0.20	0.40	0.30	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530



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